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**Serial Number: 10763685**

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PALM**

**2.) See attached EAST Inventor Search  
Printout shows Inventor search terms**

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 **PALM INTRANET**

# Inventor Information for 10/763685

<b>Inventor Name</b>	<b>City</b>	<b>State/Country</b>
MOON, BYUNG JIN	PALDAL-GU	KOREA, REPUBLIC OF

<a href="#">Appln Info</a>	<a href="#">Contents</a>	<a href="#">Petition Info</a>	<a href="#">Atty/Agent Info</a>	<a href="#">Continuity/Reexam</a>	<a href="#">Foreign Data</a>	<a href="#">Invento</a>
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US 20060190207 A1	20060824	Pattern detection for integrated circuit substrates	702/117		Whitefield; Bruce J. et al.
US 20060068399 A1	20060330	Multiple bead reagent system for protein based assays with optimized matrices	435/6	435/7.1	McMillan; William A. et al.
US 20060056252 A1	20060316	Memory device having open bit line cell structure using burn-in testing scheme and method therefor	365/205		Park; Ki-Won et al.
US 20060028900 A1	20060209	MEMORY DEVICE EMPLOYING OPEN BIT LINE ARCHITECTURE FOR PROVIDING IDENTICAL DATA TOPOLOGY ON REPAIRED MEMORY CELL BLOCK AND METHOD THEREOF	365/230.06	365/189.07; 365/200; 365/203	Shin; Dong-Hak et al.
US 20060002204 A1	20060105	Redundancy program circuit and methods thereof	365/200		Nam; Jeong-Sik et al.
US 20050136181 A1	20050623	Method of dispersing and coating additive on dielectric ceramic powder	427/221		Jung, Han Seong et al.
US 20050084185 A1	20050421	Synthetic resin bag for grain or feed	383/116	383/105; 383/117	Moon, Byung Jin
US 20050069898 A1	20050331	Lyophilized beads containing mannitol	435/6	435/182; 435/91.2	Moon, Byung Sook et al.
US 20050062543 A1	20050324	Optical dispersion correction in transimpedance amplifiers	330/308		Mayampurath, Balagopal et al.
US 20040262259 A1	20041230	Method for manufacturing semiconductor laser	216/24		Kim, Dong Joon et al.

		device			
US 20040226681 A1	20041118	Apparatus for manufacturing magnesium-alloy plate by wheel-band continuous casting, and manufacturing method thereof	164/482	164/434; 164/439; 164/488	You, Bong-Sun et al.
US 20040198024 A1	20041007	Method for cutting semiconductor wafer using laser scribing process	438/463		Yoon, Jeong Goo et al.
US 20040101859 A1	20040527	Compositions, methods and kits for polynucleotide amplification reactions and microfluidic devices	435/6	435/91.2; 516/144	Moon, Byung Sook et al.
US 20030076702 A1	20030424	Semiconductor memory device having first and second memory architecture and memory system using the same	365/51		Kyung, Kye-Hyun et al.
US 20020181310 A1	20021205	Semiconductor memory device internal voltage generator and internal voltage generating method	365/226		Park, Duk-Ha et al.
US 20020021614 A1	20020221	SEMICONDUCTOR MEMORY DEVICE HAVING COLUMN REDUNDANCY SCHEME TO IMPROVE REDUNDANCY EFFICIENCY	365/230.03		Kim, Su-a et al.
US 20020005841 A1	20020117	Transmission method, receiving method, transmitter and receiver of digital video data	345/204		Jung, Won-seok et al.
US 20020005606	20020117	Apparatus for manufacturing solder	266/202	222/594	Lee, Jin-Hyung et al.

A1		balls			
US 7027339 B2	20060411	Memory device employing open bit line architecture for providing identical data topology on repaired memory cell block and method thereof	365/200	365/190	Shin; Dong-Hak et al.
US 6762948 B2	20040713	Semiconductor memory device having first and second memory architecture and memory system using the same	365/51	365/230.03	Kyun; Kye-hyun et al.
US 6636451 B2	20031021	Semiconductor memory device internal voltage generator and internal voltage generating method	365/226	327/530; 327/538; 365/189.07; 365/189.09	Park; Duk-ha et al.
US 6569378 B2	20030527	Apparatus for manufacturing solder balls	266/202	222/594; 228/262	Lee; Jin-Hyung et al.
US 6523122 B1	20030218	Computer system for displaying system state information including advanced configuration and power interface states on a second display	713/300	713/320; 713/324	Moon; Byung-Do
US 6414896 B1	20020702	Semiconductor memory device having column redundancy scheme to improve redundancy efficiency	365/230.03	365/200	Kim; Su-a et al.
US 6366155 B1	20020402	Reference voltage generators and methods including supplementary current generation, and integrated	327/530	327/538	Moon; Byung-sick et al.

		circuits including the same			
US 6362995 B1	20020326	Arrangements of interface logic, memory core, data shift and pad blocks for integrated circuit memory devices	365/51	365/194; 365/220; 365/221; 365/230.03; 365/233; 365/63	Moon; Byung-mo et al.
US 6326833 B1	20011204	Highly effective charge pump employing NMOS transistors	327/536		Moon; Byung-sick
US 6312498 B1	20011106	Method of manufacturing solder balls	75/335	222/593; 222/594; 266/236; 75/331; 75/953	Lee; Jin-Hyung et al.
US 6304500 B1	20011016	Integrated circuit memory devices having data input and output lines extending in the column direction, and circuits and methods for repairing faulty cells	365/200	365/230.03; 365/63	Kyung; Kye-hyun et al.
US 6293888 B1	20010925	Wide ratio coverage continuously variable transmission	475/210		Moon; Byung Il
US 6261198 B1	20010717	Continuously variable transmission	475/36		Moon; Byung Il et al.
US 6225379 B1	20010501	Epoxy resin composition for bonding semiconductor chips	523/457	257/E23.04; 523/458	Kwak; Jae-Sung et al.
US 6219298 B1	20010417	High-speed address decoders and related address decoding methods	365/230.06	365/193	Hur; Nak-won et al.
US 6163498 A	20001219	Methods and systems for column line selection in a memory device	365/230.06	365/189.05; 365/194	Moon; Byung-sick
US 6151263 A	20001121	Integrated circuit memory devices having data input	365/230.03	365/63	Kyung; Kye-hyun et al.

		and output lines extending along the column direction			
US 6078536 A	20000620	Packet type integrated circuit memory devices having pins assigned direct test mode and associated methods	365/201	365/230.06	Moon; Byung-sick et al.
US 5881114 A	19990309	Error detecting circuit of a system time clock for an MPEG system decoder	375/376	370/253; 375/359; 375/368	Moon; Byung-Joon
US 5789992 A	19980804	Method and apparatus for generating digital pulse width modulated signal using multiplied component and data signals	332/109	375/238	Moon; Byung-Joon
US 5666458 A	19970909	Reproduction error correction circuit for a video reproduction system, and the method for operating it	386/2	386/20; 386/41; 386/47; 386/90	Moon; Byung-joon et al.
US 5587804 A	19961224	Reproduction error correction circuit for a video reproduction system & the method for operating it	386/2	386/20; 386/47; 386/90	Moon; Byung-Joon et al.
US D331937 S	19921222	Film changing bag	D16/237	396/590; D16/246	Moon; Byungmoon
US 4985721 A	19910115	Film change bag	396/591	190/107; 190/127; 383/119; 396/590	Moon; Byungmoon